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18. The method of claim **16** wherein the seed regions comprise stacking faults with a concentration greater than 1 cm^{-1} .

19. The method of claim **16** wherein the period of the seed regions and coalescence fronts is between about 2 microns and about 5000 microns.

20. The method of claim **16** wherein electrical contacts are placed on a defective region, wherein the defective region is selected from a seed region, a region having coalescence fronts, and a region having stacking faults at a concentration of at least 10^1 cm^{-1} .

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